

Seongil Im

List of Publications by Year in descending order

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81743

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#	ARTICLE	IF	CITATIONS
1	Damage-Free Charge Transfer Doping of 2D Transition Metal Dichalcogenide Channels by van der Waals Stamping of MoO ₃ and LiF. Small Methods, 2022, , 2101073.	4.6	2
2	Ferroelastic-Ferroelectric Multiferroicity in van der Waals Rhenium Dichalcogenides. Advanced Materials, 2022, 34, e2108777.	11.1	10
3	Engineering MoSe ₂ /MoS ₂ heterojunction traps in 2D transistors for multilevel memory, multiscale display, and synaptic functions. Npj 2D Materials and Applications, 2022, 6, .	3.9	23
4	Quaternary NAND Logic and Complementary Ternary Inverter with p-MoS ₂ /n-MoS ₂ Heterostack Channel Transistors. Advanced Functional Materials, 2022, 32, .	7.8	14
5	Density-Dependent Microstructures and Electromechanical Properties of Amorphous InGaZnO ₄ Semiconductors: An Ab Initio Study. ACS Applied Electronic Materials, 2022, 4, 2545-2551.	2.0	3
6	Dynamic Oscillation via Negative Differential Resistance in Type III Junction Organic/Two-Dimensional and Oxide/Two-Dimensional Transition Metal Dichalcogenide Diodes. Advanced Functional Materials, 2021, 31, 2009436.	7.8	19
7	Nanowatt use 8ÅV switching nonvolatile memory transistors with 2D MoTe ₂ channel and ferroelectric P(VDF-TrFE). Nano Energy, 2021, 81, 105686.	8.2	12
8	2D MoS ₂ Charge Injection Memory Transistors Utilizing Hetero-Stack SiO ₂ /HfO ₂ Dielectrics and Oxide Interface Traps. Advanced Electronic Materials, 2021, 7, 2100074.	2.6	8
9	High Performance ² â€Ga ₂ O ₃ Schottky Barrier Transistors with Large Work Function TMD Gate of NbS ₂ and TaS ₂ . Advanced Functional Materials, 2021, 31, 2010303.	7.8	22
10	Dramatic Reduction of Contact Resistance via Ultrathin LiF in Two-Dimensional MoS ₂ Field Effect Transistors. Nano Letters, 2021, 21, 3503-3510.	4.5	18
11	Hydrogen Barriers Based on Chemical Trapping Using Chemically Modulated Al ₂ O ₃ Grown by Atomic Layer Deposition for InGaZnO Thin-Film Transistors. ACS Applied Materials & Interfaces, 2021, 13, 20349-20360.	4.0	15
12	Single-Crystalline Metallic Films Induced by van der Waals Epitaxy on Black Phosphorus. Chemistry of Materials, 2021, 33, 3593-3601.	3.2	6
13	Ambipolar Channel p-TMD/n-Ga ₂ O ₃ Junction Field Effect Transistors and High Speed Photo-sensing in TMD Channel. Advanced Materials, 2021, 33, e2103079.	11.1	28
14	Near-Infrared Self-Powered Linearly Polarized Photodetection and Digital Incoherent Holography Using WSe ₂ /ReSe ₂ van der Waals Heterostructure. ACS Nano, 2021, 15, 17917-17925.	7.3	46
15	Low Voltage and Ferroelectric 2D Electron Devices Using Lead-Free Ba x Sr 1-x TiO ₃ and MoS ₂ Channel. Advanced Functional Materials, 2020, 30, 1908210.	7.8	16
16	Complementary Type Ferroelectric Memory Transistor Circuits with p- and n-Channel MoTe ₂ . Advanced Electronic Materials, 2020, 6, 2000479.	2.6	12
17	Zero-Dimensional PbS Quantum Dot-InGaZnO Film Heterostructure for Short-Wave Infrared Flat-Panel Imager. ACS Photonics, 2020, 7, 1932-1941.	3.2	26
18	High-Performance van der Waals Junction Field-Effect Transistors Utilizing Organic Molecule/Transition Metal Dichalcogenide Interface. ACS Nano, 2020, 14, 15646-15653.	7.3	6

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19	2D TMD Channel Transistors with ZnO Nanowire Gate for Extended Nonvolatile Memory Applications. <i>Advanced Functional Materials</i> , 2020, 30, 2004140.	7.8	24
20	Nonvolatile and Neuromorphic Memory Devices Using Interfacial Traps in Two-Dimensional WSe ₂ /MoTe ₂ Stack Channel. <i>ACS Nano</i> , 2020, 14, 12064-12071.	7.3	38
21	Tungsten Dichalcogenide Nanoflake/InGaZnO Thin-Film Heterojunction for Photodetector, Inverter, and AC Rectifier Circuits. <i>Advanced Electronic Materials</i> , 2020, 6, 2000026.	2.6	7
22	Ultrafast 27%GHz cutoff frequency in vertical WSe ₂ Schottky diodes with extremely low contact resistance. <i>Nature Communications</i> , 2020, 11, 1574.	5.8	39
23	Self-Powered Visible-Invisible Multiband Detection and Imaging Achieved Using High-Performance 2D MoTe ₂ /MoS ₂ Semivertical Heterojunction Photodiodes. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 10858-10866.	4.0	49
24	Stability, efficiency, and mechanism of n -type doping by hydrogen adatoms in two-dimensional transition metal dichalcogenides. <i>Physical Review B</i> , 2019, 100, .	1.1	12
25	Impact of δ -Doping on n -type TMD Channels for Low-Temperature Band-Like Transport. <i>Small</i> , 2019, 15, e1901793.	5.2	11
26	All-2D ReS ₂ transistors with split gates for logic circuitry. <i>Scientific Reports</i> , 2019, 9, 10354.	1.6	22
27	Seamless MoTe ₂ Homojunction PIN Diode toward 1300 nm Short-Wave Infrared Detection. <i>Advanced Optical Materials</i> , 2019, 7, 1900768.	3.6	20
28	Advanced Multifunctional Field Effect Devices Using Common Gate for Both 2D Transition-Metal Dichalcogenide and InGaZnO Channels. <i>Advanced Electronic Materials</i> , 2019, 5, 1900730.	2.6	12
29	Intrinsic Correlation between Electronic Structure and Degradation: From Few-Layer to Bulk Black Phosphorus (Angew. Chem. 12/2019). <i>Angewandte Chemie</i> , 2019, 131, 4107-4107.	1.6	3
30	Integrated advantages from perovskite photovoltaic cell and 2D MoTe ₂ transistor towards self-power energy harvesting and photosensing. <i>Nano Energy</i> , 2019, 63, 103833.	8.2	19
31	ZnO composite nanolayer with mobility edge quantization for multi-value logic transistors. <i>Nature Communications</i> , 2019, 10, 1998.	5.8	67
32	Monolayer MoS ₂ field-effect transistors patterned by photolithography for active matrix pixels in organic light-emitting diodes. <i>Npj 2D Materials and Applications</i> , 2019, 3, .	3.9	43
33	Impact of Organic Molecule-Induced Charge Transfer on Operating Voltage Control of Both n-MoS ₂ and p-MoTe ₂ Transistors. <i>Nano Letters</i> , 2019, 19, 2456-2463.	4.5	26
34	Intrinsic Correlation between Electronic Structure and Degradation: From Few-Layer to Bulk Black Phosphorus. <i>Angewandte Chemie</i> , 2019, 131, 3794-3798.	1.6	6
35	Intrinsic Correlation between Electronic Structure and Degradation: From Few-Layer to Bulk Black Phosphorus. <i>Angewandte Chemie - International Edition</i> , 2019, 58, 3754-3758.	7.2	26
36	Vertical and In-Plane Current Devices Using NbS ₂ /n-MoS ₂ van der Waals Schottky Junction and Graphene Contact. <i>Nano Letters</i> , 2018, 18, 1937-1945.	4.5	86

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37	Polymer/oxide bilayer dielectric for hysteresis-minimized 1ÅV operating 2D TMD transistors. RSC Advances, 2018, 8, 2837-2843.	1.7	10
38	Charge-Transfer-Induced p-Type Channel in MoS ₂ Flake Field Effect Transistors. ACS Applied Materials & Interfaces, 2018, 10, 4206-4212.	4.0	25
39	Van der Waals junction field effect transistors with both n- and p-channel transition metal dichalcogenides. Npj 2D Materials and Applications, 2018, 2, .	3.9	66
40	High-Performance 2D MoS ₂ Phototransistor for Photo Logic Gate and Image Sensor. ACS Photonics, 2018, 5, 4745-4750.	3.2	43
41	Direct Thermal Growth of Large Scale Cl-doped CdTe Film for Low Voltage High Resolution X-ray Image Sensor. Scientific Reports, 2018, 8, 14810.	1.6	16
42	2D WSe ₂ /MoS ₂ van der Waals heterojunction photodiode for visible-near infrared broadband detection. Applied Physics Letters, 2018, 113, .	1.5	60
43	High-Responsivity Multilayer MoSe ₂ Phototransistors with Fast Response Time. Scientific Reports, 2018, 8, 11545.	1.6	48
44	Fully Transparent p-MoTe ₂ 2D Transistors Using Ultrathin MoO _x /Pt Contact Media for Indium-Tin-Oxide Source/Drain. Advanced Functional Materials, 2018, 28, 1801204.	7.8	25
45	2D MoSe ₂ Transistor with Polymer-Brush/Channel Interface. Advanced Materials Interfaces, 2018, 5, 1800812.	1.9	30
46	Few-layered 1±-MoTe ₂ Schottky junction for a high sensitivity chemical-vapour sensor. Journal of Materials Chemistry C, 2018, 6, 10714-10722.	2.7	25
47	Interband Transitions in Monolayer and Few-Layer WSe ₂ Probed Using Photoexcited Charge Collection Spectroscopy. ACS Applied Materials & Interfaces, 2018, 10, 20213-20218.	4.0	8
48	Work Function Tuning in Two-Dimensional MoS ₂ Field-Effect-Transistors with Graphene and Titanium Source-Drain Contacts. Scientific Reports, 2017, 7, 45546.	1.6	33
49	Coupling Two-Dimensional MoTe ₂ and InGaZnO Thin-Film Materials for Hybrid PN Junction and CMOS Inverters. ACS Applied Materials & Interfaces, 2017, 9, 15592-15598.	4.0	32
50	Mixed-Dimensional 1D ZnO-2D WSe ₂ van der Waals Heterojunction Device for Photosensors. Advanced Functional Materials, 2017, 27, 1703822.	7.8	98
51	Charge Transport in 2D DNA Tunnel Junction Diodes. Small, 2017, 13, 1703006.	5.2	13
52	Transition Metal Dichalcogenide-Based Transistor Circuits for Gray Scale Organic Light-Emitting Displays. Advanced Functional Materials, 2017, 27, 1603682.	7.8	31
53	Homogeneous 2D MoTe ₂ p-n Junctions and CMOS Inverters formed by Atomic-Layer-Deposition-Induced Doping. Advanced Materials, 2017, 29, 1701798.	11.1	117
54	Nonvolatile Charge Injection Memory Based on Black Phosphorous 2D Nanosheets for Charge Trapping and Active Channel Layers. Advanced Functional Materials, 2016, 26, 5701-5707.	7.8	49

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55	Non-Lithographic Fabrication of All-2D MoTe_2 Dual Gate Transistors. <i>Advanced Functional Materials</i> , 2016, 26, 3146-3153.	7.8	55
56	Electric and Photovoltaic Behavior of a Few-Layer MoTe_2 / MoS_2 Dichalcogenide Heterojunction. <i>Advanced Materials</i> , 2016, 28, 3216-3222.	11.1	236
57	Self-Limiting Layer Synthesis of Transition Metal Dichalcogenides. <i>Scientific Reports</i> , 2016, 6, 18754.	1.6	74
58	Large scale MoS_2 nanosheet logic circuits integrated by photolithography on glass. <i>2D Materials</i> , 2016, 3, 044001.	2.0	26
59	Transition metal dichalcogenide heterojunction PN diode toward ultimate photovoltaic benefits. <i>2D Materials</i> , 2016, 3, 045011.	2.0	45
60	Deep blue energy harvest photovoltaic switching by heptazole-based organic Schottky diode circuits. <i>NPG Asia Materials</i> , 2016, 8, e278-e278.	3.8	7
61	Enhanced Non-enzymatic amperometric sensing of glucose using $\text{Co}(\text{OH})_2$ nanorods deposited on a three dimensional graphene network as an electrode material. <i>Mikrochimica Acta</i> , 2016, 183, 2473-2479.	2.5	29
62	Black Phosphorus-Zinc Oxide Nanomaterial Heterojunction for p^+n Diode and Junction Field-Effect Transistor. <i>Nano Letters</i> , 2016, 16, 1293-1298.	4.5	141
63	Static and Dynamic Performance of Complementary Inverters Based on Nanosheet MoTe_2 p^+i -Channel and MoS_2 i -Channel Transistors. <i>ACS Nano</i> , 2016, 10, 1118-1125.	7.3	98
64	Reply to "Comment on "Metal Semiconductor Field-Effect Transistor with MoS_2 /Conducting NiO_x van der Waals Schottky Interface for Intrinsic High Mobility and Photoswitching Speed". <i>ACS Nano</i> , 2016, 10, 1716-1717.	7.3	0
65	Ultrasensitive PbS quantum-dot-sensitized InGaZnO hybrid photoinverter for near-infrared detection and imaging with high photogain. <i>NPG Asia Materials</i> , 2016, 8, e233-e233.	3.8	129
66	High-Performance, Air-Stable, Top-Gate, p^+i -Channel WSe_2 Field-Effect Transistor with Fluoropolymer Buffer Layer. <i>Advanced Functional Materials</i> , 2015, 25, 7208-7214.	7.8	67
67	Columnar deformation of human red blood cell by highly localized fiber optic Bessel beam stretcher. <i>Biomedical Optics Express</i> , 2015, 6, 4417.	1.5	11
68	High-Gain Subnanowatt Power Consumption Hybrid Complementary Logic Inverter with WSe_2 Nanosheet and ZnO Nanowire Transistors on Glass. <i>Advanced Materials</i> , 2015, 27, 150-156.	11.1	43
69	Few-Layer MoS_2 "Organic Thin-Film Hybrid Complementary Inverter Pixel Fabricated on a Glass Substrate. <i>Small</i> , 2015, 11, 2132-2138.	5.2	28
70	Enhanced device performances of WSe_2 p^+i - MoS_2 van der Waals junction p^+n diode by fluoropolymer encapsulation. <i>Journal of Materials Chemistry C</i> , 2015, 3, 2751-2758.	2.7	74
71	Metal Semiconductor Field-Effect Transistor with MoS_2 /Conducting NiO_x van der Waals Schottky Interface for Intrinsic High Mobility and Photoswitching Speed. <i>ACS Nano</i> , 2015, 9, 8312-8320.	7.3	82
72	Layer dependence and gas molecule absorption property in MoS_2 Schottky diode with asymmetric metal contacts. <i>Scientific Reports</i> , 2015, 5, 10440.	1.6	49

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73	Nitrogen-doped ZnO/n-Si core-shell nanowire photodiode prepared by atomic layer deposition. <i>Materials Science in Semiconductor Processing</i> , 2015, 33, 154-160.	1.9	19
74	Analysis of Self-Heating Effect on Short Channel Amorphous InGaZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2015, 36, 472-474.	2.2	19
75	Low Power Consumption Complementary Inverters with n-MoS ₂ and p-WSe ₂ Dichalcogenide Nanosheets on Glass for Logic and Light-Emitting Diode Circuits. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 22333-22340.	4.0	113
76	Nonvolatile Ferroelectric Memory Circuit Using Black Phosphorus Nanosheet-Based Field-Effect Transistors with P(VDF-TrFE) Polymer. <i>ACS Nano</i> , 2015, 9, 10394-10401.	7.3	130
77	Wafer-scale single-domain-like graphene by defect-selective atomic layer deposition of hexagonal ZnO. <i>Nanoscale</i> , 2015, 7, 17702-17709.	2.8	19
78	Comparative studies on ZnO thin-film transistors with inorganic versus polymer dielectric interfaces. <i>Journal of the Korean Physical Society</i> , 2015, 67, 537-540.	0.3	0
79	Dual Gate Black Phosphorus Field Effect Transistors on Glass for NOR Logic and Organic Light Emitting Diode Switching. <i>Nano Letters</i> , 2015, 15, 5778-5783.	4.5	83
80	High-performance a MoS ₂ nanosheet-based nonvolatile memory transistor with a ferroelectric polymer and graphene source-drain electrode. <i>Journal of the Korean Physical Society</i> , 2015, 67, 1499-1503.	0.3	25
81	Origin of channel/dielectric interfacial trap states modification by ultraviolet irradiation on organic thin-film transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014, 211, 2886-2889.	0.8	1
82	3-D Manipulation of ZnO Nanowire Using Optically Activated Thermoplastic Tip on Silica Fiber Taper. <i>IEEE Photonics Technology Letters</i> , 2014, 26, 2001-2003.	1.3	0
83	Highly Sensitive Non-Classical Strain Gauge Using Organic Heptazole Thin-Film Transistor Circuit on a Flexible Substrate. <i>Advanced Functional Materials</i> , 2014, 24, 4413-4419.	7.8	44
84	Photo-Stable Organic Thin-Film Transistor Utilizing a New Indolocarbazole Derivative for Image Pixel and Logic Applications. <i>Advanced Functional Materials</i> , 2014, 24, 1109-1116.	7.8	38
85	NiOx Schottky-gated ZnO nanowire metal-semiconductor field effect transistor: fast logic inverter and photo-detector. <i>Journal of Materials Chemistry C</i> , 2014, 2, 4428.	2.7	15
86	Top and back gate molybdenum disulfide transistors coupled for logic and photo-inverter operation. <i>Journal of Materials Chemistry C</i> , 2014, 2, 8023-8028.	2.7	26
87	Molybdenum Disulfide Nanoflake-Zinc Oxide Nanowire Hybrid Photoinverter. <i>ACS Nano</i> , 2014, 8, 5174-5181.	7.3	21
88	MoS ₂ nanosheet channel and guanine DNA-base charge injection layer for high performance memory transistors. <i>Journal of Materials Chemistry C</i> , 2014, 2, 5411-5416.	2.7	22
89	Organic Field-Effect Transistors: Critical Factors to Achieve Low Voltage- and Capacitance-Based Organic Field-Effect Transistors (Adv. Mater. 2/2014). <i>Advanced Materials</i> , 2014, 26, 194-194.	11.1	0
90	Direct imprinting of MoS ₂ flakes on a patterned gate for nanosheet transistors. <i>Journal of Materials Chemistry C</i> , 2013, 1, 7803.	2.7	50

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91	Instability of amorphous hafnium-indium-zinc-oxide thin film transistors under negative-bias-illumination stress. Applied Physics Letters, 2013, 102, .	1.5	3
92	Manipulating ZnO nanowires for field-effect device integration by optical-fiber grip coated with thermoplastic copolymer. Journal of Materials Chemistry C, 2013, 1, 7303.	2.7	4
93	All-fiber 1-D optical stretcher for bio-cells implemented in a Lab-on-a-Chip. , 2013, , .		1
94	Origin of Bias-Stress Induced Instability in Organic Thin-Film Transistors with Semiconducting Small-Molecule/Insulating Polymer Blend Channel. ACS Applied Materials & Interfaces, 2013, 5, 1625-1629.	4.0	31
95	NOT and NOR Logic Circuits Using Passivation Dielectric Involved Dual Gate in a-InGaZnO TFTs. IEEE Electron Device Letters, 2013, 34, 1527-1529.	2.2	8
96	Annealing-induced conductivity transition in ZnO nanowires for field-effect devices. Applied Physics Letters, 2012, 101, 043504.	1.5	10
97	n-ZnO:N/p-Si nanowire photodiode prepared by atomic layer deposition. Applied Physics Letters, 2012, 100, .	1.5	32
98	Photoexcited charge collection spectroscopy of two-dimensional polaronic states in polymer thin-film transistors. Physical Review B, 2012, 85, .	1.1	15
99	Transparent p-n-ZnO diodes used in circuit rectifiers. Physica Status Solidi - Rapid Research Letters, 2012, 6, 475-477.	1.2	5
100	MoS ₂ Nanosheets for Top-Gate Nonvolatile Memory Transistor Channel. Small, 2012, 8, 3111-3115.	5.2	219
101	Data Storage: MoS ₂ Nanosheets for Top-Gate Nonvolatile Memory Transistor Channel (Small 20/2012). Small, 2012, 8, 3220-3220.	5.2	0
102	ZnO nanowire manipulation and transportation using thermoplastic and tapered silica nanowire. , 2012, , .		1
103	Ambient-protecting organic light transducer grown on pentacene-channel of photo-gating complementary inverter. Journal of Materials Chemistry, 2012, 22, 4444.	6.7	6
104	Organic-inorganic nanohybrid nonvolatile memory transistors for flexible electronics. Journal of Materials Chemistry, 2012, 22, 19007.	6.7	12
105	Capacitance-Voltage Measurement With Photon Probe to Quantify the Trap Density of States in Amorphous Thin-Film Transistors. IEEE Electron Device Letters, 2012, 33, 1015-1017.	2.2	15
106	MoS ₂ Nanosheet Phototransistors with Thickness-Modulated Optical Energy Gap. Nano Letters, 2012, 12, 3695-3700.	4.5	1,221
107	The effects of surface modification on the electrical properties of n + junction silicon nanowires grown by an aqueous electroless etching method. Journal of Nanoparticle Research, 2012, 14, 1.	0.8	4
108	The Influence of In/Zn Ratio on the Performance and Negative-Bias Instability of Hf-In-Zn-O Thin-Film Transistors Under Illumination. IEEE Electron Device Letters, 2011, 32, 1251-1253.	2.2	18

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109	DC Versus Pulse-Type Negative Bias Stress Effects on the Instability of Amorphous InGaZnO Transistors Under Light Illumination. IEEE Electron Device Letters, 2011, 32, 1704-1706.	2.2	20
110	ZnO nanowire transistor inverter using top-gate electrodes with different work functions. Applied Physics Letters, 2011, 99, 153507.	1.5	13
111	Self-assembled organic channel~polymer dielectric layer for organic thin-film transistor applications. AIP Conference Proceedings, 2011, , .	0.3	0
112	Single-Crystalline Silicon-Based Heterojunction Photodiode Arrays on Flexible Plastic Substrates. IEEE Transactions on Electron Devices, 2011, 58, 3329-3334.	1.6	7
113	Threshold voltage control by gate electrode in Ga-Sn-Zn-O thin-film transistors for logic inverter application. Physica Status Solidi - Rapid Research Letters, 2011, 5, 211-213.	1.2	3
114	Sputter~deposited Ga~Sn~Zn~O thin films for transparent thin film transistors. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 2934-2938.	0.8	4
115	Photogating and electrical-gating of amorphous GaSnZnO-based inverter with light-transmitting gate electrode. Applied Physics Letters, 2011, 98, 223505.	1.5	5
116	Nonvolatile memory properties in ZnO-based thin-film transistors with polymer ferroelectric and thin buffer layer. , 2010, , .		1
117	Ferroelectric property improvement of poly(vinylidene fluoride/trifluoroethylene) polymer exposed to a plasma ambient. Applied Physics Letters, 2010, 97, 162911.	1.5	2
118	ZnO nanowire and mesowire for logic inverter fabrication. Applied Physics Letters, 2010, 97, 123506.	1.5	19
119	The influence of sputtering power and O2/Ar flow ratio on the performance and stability of Hf~In~Zn~O thin film transistors under illumination. Applied Physics Letters, 2010, 97, 102103.	1.5	30
120	Density of trap states measured by photon probe into ZnO based thin-film transistors. Applied Physics Letters, 2010, 97, .	1.5	30
121	Quantitative photon-probe evaluation of trap-containing channel/dielectric interface in organic field effect transistors. Journal of Materials Chemistry, 2010, 20, 2659.	6.7	12
122	Low-voltage pentacene transistor inverters using micro-contact printed nano-layer. Journal of Materials Chemistry, 2010, 20, 663-665.	6.7	4
123	Channel/ferroelectric interface modification in ZnO non-volatile memoryTFT with P(VDF-TrFE)polymer. Journal of Materials Chemistry, 2010, 20, 2638-2643.	6.7	21
124	Enhancing the retention properties of ZnO memory transistor by modifying the channel/ferroelectric polymer interface. Applied Physics Letters, 2009, 95, 153502.	1.5	32
125	Terahertz time-domain spectroscopy of NiO<inf>x</inf> thin films. , 2009, , .		0
126	The effect of localized surface plasmon on the photocurrent of silicon nanocrystal photodetectors. Applied Physics Letters, 2009, 94, 183108.	1.5	22

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127	Transparent Photo-Stable Complementary Inverter with an Organic/Inorganic Nanohybrid Dielectric Layer. <i>Advanced Functional Materials</i> , 2009, 19, 726-732.	7.8	41
128	Thin-Film Transistors: Transparent Photo-Stable Complementary Inverter with an Organic/Inorganic Nanohybrid Dielectric Layer (<i>Adv. Funct. Mater.</i> 5/2009). <i>Advanced Functional Materials</i> , 2009, 19, NA-NA.	7.8	0
129	Transparent and Photo-Stable ZnO Thin-film Transistors to Drive an Active Matrix Organic-Light-Emitting-Diode Display Panel. <i>Advanced Materials</i> , 2009, 21, 678-682.	11.1	383
130	Dual Gate ZnO-Based Thin-Film Transistors Operating at 5 V: nor Gate Application. <i>IEEE Electron Device Letters</i> , 2009, 30, 30-32.	2.2	26
131	Transparent photostable ZnO nonvolatile memory transistor with ferroelectric polymer and sputter-deposited oxide gate. <i>Applied Physics Letters</i> , 2009, 95, 223506.	1.5	31
132	42.3: Transparent ZnO Thin Film Transistor for the Application of High Aperture Ratio Bottom Emission AMOLED Display. <i>Digest of Technical Papers SID International Symposium</i> , 2008, 39, 629-632.	0.1	34
133	Determining the optimum pentacene channel thickness on hydrophobic and hydrophilic dielectric surface. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	18
134	Infrared spectroscopy of the interface charge in a ZnO field-effect transistor. <i>Applied Physics Letters</i> , 2008, 93, 241902.	1.5	8
135	ZnO-based low voltage inverter with low-k/high-k double polymer dielectric layer. <i>Applied Physics Letters</i> , 2008, 93, 193514.	1.5	18
136	High-k and low-k nanocomposite gate dielectrics for low voltage organic thin film transistors. <i>Applied Physics Letters</i> , 2006, 88, 243515.	1.5	37
137	Reliable semi-transparent pentacene thin-film transistors with polymer gate dielectric layers cured at an optimum temperature. <i>Materials Research Society Symposia Proceedings</i> , 2005, 905, 1.	0.1	0
138	Passivation effects on the stability of pentacene thin-film transistors with SnO ₂ prepared by ion-beam-assisted deposition. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 2357.	1.6	14
139	ZnO-based thin-film transistors of optimal device performance. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2004, 22, 1191.	1.6	34
140	Effects of substrate temperature on the device properties of pentacene-based thin film transistors using Al ₂ O _{3+x} gate dielectric. <i>Journal of Applied Physics</i> , 2004, 95, 3733-3736.	1.1	63
141	Correlation between photoelectric and optical absorption spectra of thermally evaporated pentacene films. <i>Applied Physics Letters</i> , 2004, 84, 1701-1703.	1.5	109
142	Ultraviolet-enhanced photodiode employing n-ZnO/p-Si structure. <i>Applied Physics Letters</i> , 2003, 83, 2946-2948.	1.5	368
143	Spectral responsivity and quantum efficiency of n-ZnO/p-Si photodiode fully isolated by ion-beam treatment. <i>Applied Physics Letters</i> , 2003, 82, 3973-3975.	1.5	59
144	Photodetecting properties of ZnO-based thin-film transistors. <i>Applied Physics Letters</i> , 2003, 83, 5313-5315.	1.5	170

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145	Pentacene thin-film transistors with Al ₂ O _{3+x} gate dielectric films deposited on indium-tin-oxide glass. Applied Physics Letters, 2003, 83, 2689-2691.	1.5	94
146	Fabrication of p-pentacene/n-Si organic photodiodes and characterization of their photoelectric properties. Applied Physics Letters, 2003, 82, 639-641.	1.5	54
147	Electrical properties of aluminum oxide films deposited on indium-tin-oxide glasses. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 953.	1.6	20
148	Hole transport in amorphous-crystalline-mixed and amorphous pentacene thin-film transistors. Applied Physics Letters, 2002, 81, 4640-4642.	1.5	35
149	Room Temperature Cmcm Phase of C _x Sn _{1-x} Se for Thermoelectric Energy Conversion. ACS Applied Energy Materials, 0, , .	2.5	2